

< C band internally matched power GaAs FET >

MGFC36V4450A

4.4 - 5.0 GHz BAND / 4W

DESCRIPTION

The MGFC36V4450A is an internally impedance-matched GaAs power FET especially designed for use in 4.4 - 5.0 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation

Internally matched to 50(ohm) system • High output power

- P1dB=4W (TYP.) @f=4.4 5.0GHz • High power gain
- GLP=12dB (TYP.) @f=4.4 5.0GHz • High power added efficiency
- P.A.E.=32% (TYP.) @f=4.4 5.0GHz • Low distortion [item -51]
- IM3=-45dBc (TYP.) @Po=25dBm S.C.L

APPLICATION

- item 01 : 4.4 5.0 GHz band power amplifier
- \bullet item 51 : 4.4 5.0 GHz band digital radio communication

QUALITY

• IG

RECOMMENDED BIAS CONDITIONS

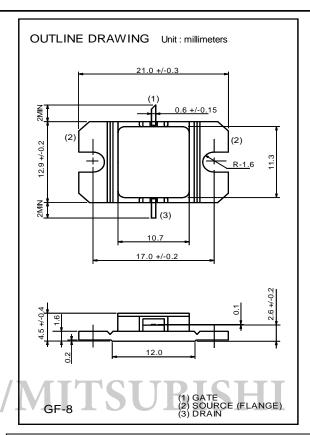
VDS=10V
ID=1.2A
Refer to Bias Procedure
RG=100ohm

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain breakdown voltage	-15	V
VGSO	Gate to source breakdown voltage	-15	V
ID	Drain current	3.75	А
IGR	Reverse gate current	-10	mA
IGF	Forward gate current	21	mA
PT *1	Total power dissipation	25	W
Tch	Cannel temperature	175	°C
Tstg	Storage temperature	-65 to +175	°C

*1 : Tc=25°C

Electrical characteristics (Ta=25°C)



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Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	-	3.75	А
gm	Transconductance	VDS=3V,ID=1.1A	-	1	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=10mA	-	-	-4.5	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=1.2A	35	37	-	dBm
GLP	Linear Power Gain	f=4.4 – 5.0GHz	11	12	-	dB
ID	Drain current		-	-	1.8	А
P.A.E.	Power added efficiency		-	32	-	%
IM3 *2	3rd order IM distortion	7	-42	-45	-	dBc
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	5	6	°C/W

*2 :item -51 ,2 tone test,Po=25dBm Single Carrier Level ,f=5.0GHz,delta f=10MHz

*3 :Channel-case

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